

Power Schottky Rectifier - 1Amp 40~200Volt

Features

- For surface mounted applications
- Low profile package
- Built-in strain relief
- Metal silicon junction, majority carrier conduction
- Low power loss, high efficiency
- High current capability, low forward voltage drop
- High temperature soldering guaranteed
- High reliability
- High surge current capability
- Epitaxial construction
- Lead free device
- ESD sensitive product handling required

Mechanical data

- Case : Molded plastic
- Epoxy : UL 94V-0 rate flame retardant
- Terminals : Solder plated, solderable per MIL-STD-750,method 2026
- Polarity : Color band denotes cathode end

Maximum ratings and Electrical characteristics

Parameters	MBR140	MBR160	MBR1100	MBR1150	MBR1200	UNIT
Maximum Recurrent Peak Reverse Voltage	40	60	100	150	200	V
Maximum RMS Voltage	28	42	70	105	140	V
Maximum DC Blocking Voltage	40	60	100	150	200	V
Maximum Average Forward Rectified Current	1					A
Peak Forward Surge Current	30					A
Maximum Instantaneous Forward Voltage at 1A	Tc = 25°C	0.50	0.65	0.8	0.85	V
	Tc = 125°C	0.40	0.50	0.66	0.69	
Maximum Average Reverse Current at Rated DC Blocking Voltage	Tc = 25°C	0.5		0.05		mA
	Tc = 100°C	20		10		
Typical Junction Capacitance	110					pF
Typical Thermal Resistance R _{θJL}	30					°C/W
Operating and Storage Temperature Range	-50 to +125		-50 to +150			°C

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MBR140 ~ MBR1200

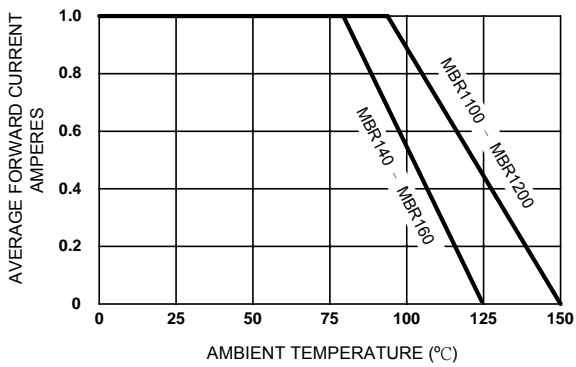


Figure 1. Forward Current Derating Curve

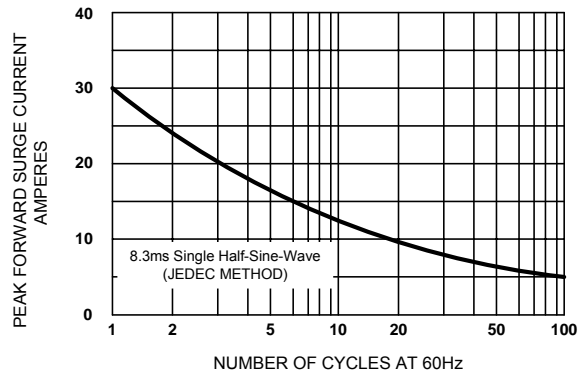


Figure 2. Maximum Non-repetitive Surge Current

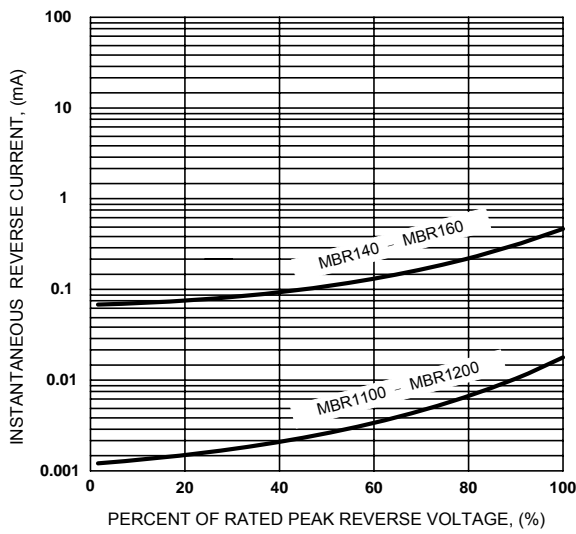


Figure 3. Typical Reverse Characteristics

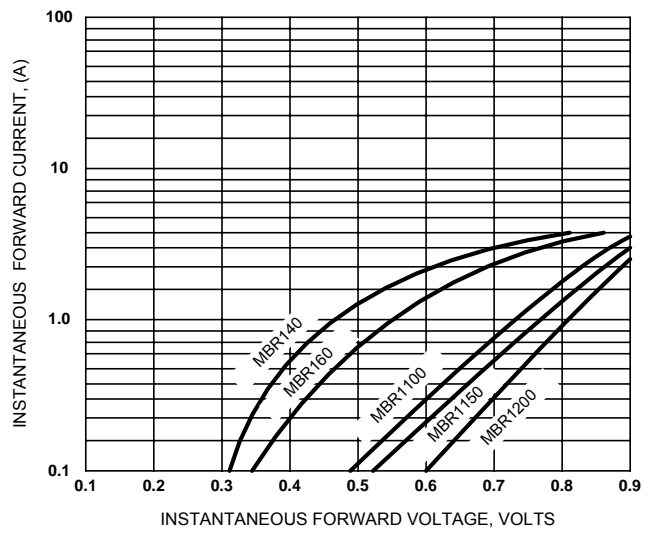


Figure 4. Typical Forward Characteristics

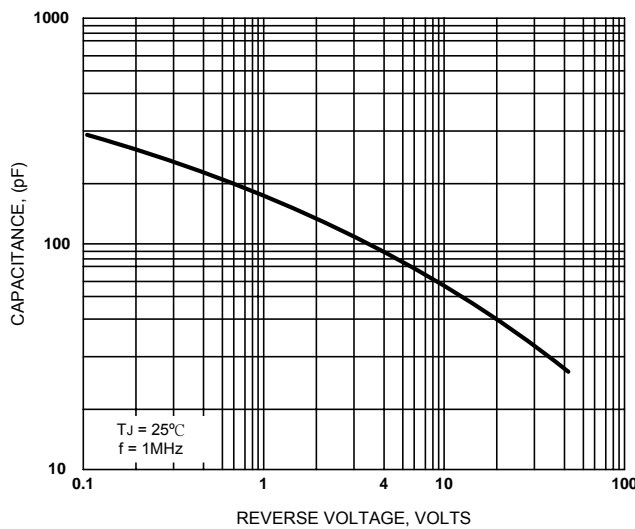


Figure 5. Typical Junction Capacitance



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